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## AMENDMENT TO THE CLAIMS

1-18 (Canceled).

19. (Currently Amended) An array substrate for an active matrix type liquid crystal display

(LCD) device, comprising:

a substrate;

a gate line on said substrate, wherein said gate line includes a gate pad;

a first insulating layer on said gate line and said substrate;

a semiconductor layer on said first insulating layer and over a portion of said gate line;

a data line over said first insulating layer and that crosses said gate line, said data line

including a protruding portion that projects in a direction of said semiconductor layer and that

forms a source electrode, wherein an end portion of the semiconductor layer under the data line

coincides to is substantially a same width as an end portion of the data line, wherein said data

line further includes a data pad;

a drain electrode spaced apart from said source electrode and extending into a

rectangular region partially defined by said gate and data lines;

a passivation layer on said drain electrode, said passivation layer having a drain contact

hole that exposes said drain electrode; and

a pixel electrode formed over the passivation layer, said pixel electrode electrically

connecting to said drain electrode via said drain contact hole, wherein said pixel electrode

extends over a portion of said gate line so as to form a storage capacitor comprised of said pixel

electrode, said gate line, and said first insulating layer, wherein said storage capacitor further

includes a short-preventing part disposed between said pixel electrode and said gate line.

20. (Original) The array substrate of claim 19, wherein said short-preventing part includes said

semiconductor layer and said passivation layer.

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21. (Original) The array substrate of claim 20, wherein said short-preventing part further includes an ohmic contact layer, and a conducting material between said semiconductor layer and said passivation layer.